

TOSHIBA Transistor Silicon PNP · NPN Epitaxial Type  
(PCT process) (Bias Resistor built-in Transistor)

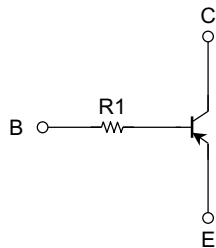
# RN4910FE

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications.

- Two devices are incorporated into an Extreme-Super-Mini (6 pin) package.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.

## Equivalent Circuit and Bias Resistor Values

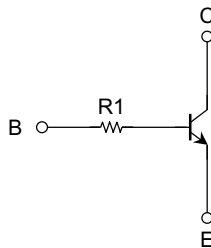
Q1



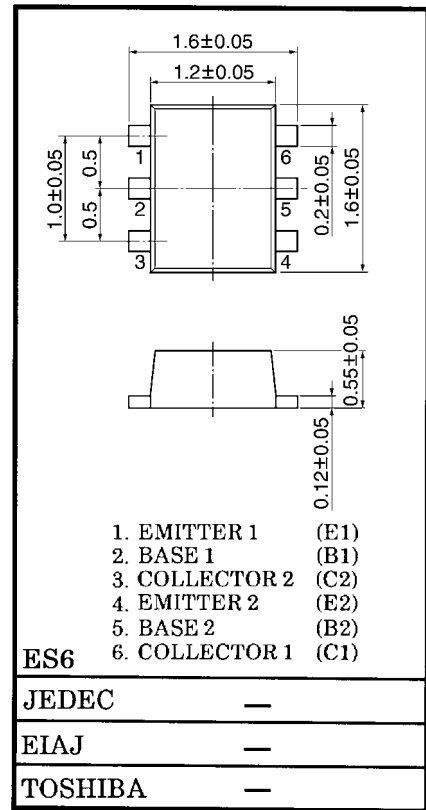
R1: 4.7 kΩ

(Q1, Q2 common)

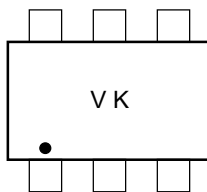
Q2



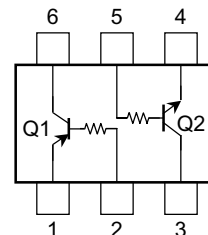
Unit in mm



## Marking



## Equivalent Circuit (top view)



000707EAA1

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**Maximum Ratings (Ta = 25°C) (Q1)**

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-100	mA

**Maximum Ratings (Ta = 25°C) (Q2)**

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	50	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	I <sub>C</sub>	100	mA

**Maximum Ratings (Ta = 25°C) (Q1, Q2 common)**

Characteristics	Symbol	Rating	Unit
Collector power dissipation	P <sub>C</sub> (Note)	100	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

Note: Total rating

## Electrical Characteristics (Ta = 25°C) (Q1)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-100	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-100	nA
DC current gain	$h_{FE}$	$V_{CE} = -5\text{ V}, I_C = -1\text{ mA}$	120	—	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -5\text{ mA}, I_B = -0.25\text{ mA}$	—	-0.1	-0.3	V
Transition frequency	$f_T$	$V_{CE} = -10\text{ V}, I_C = -5\text{ mA}$	—	200	—	MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	3	6	pF

## Electrical Characteristics (Ta = 25°C) (Q2)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = 50\text{ V}, I_E = 0$	—	—	100	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	100	nA
DC current gain	$h_{FE}$	$V_{CE} = 5\text{ V}, I_C = 1\text{ mA}$	120	—	700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 5\text{ mA}, I_B = 0.25\text{ mA}$	—	0.1	0.3	V
Transition frequency	$f_T$	$V_{CE} = 10\text{ V}, I_C = 5\text{ mA}$	—	250	—	MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	3	6	pF

## Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input resistor	R1	—	3.29	4.7	6.11	k $\Omega$